



PJA3409-AU

30V P-Channel Enhancement Mode MOSFET

Voltage

-30 V

Current

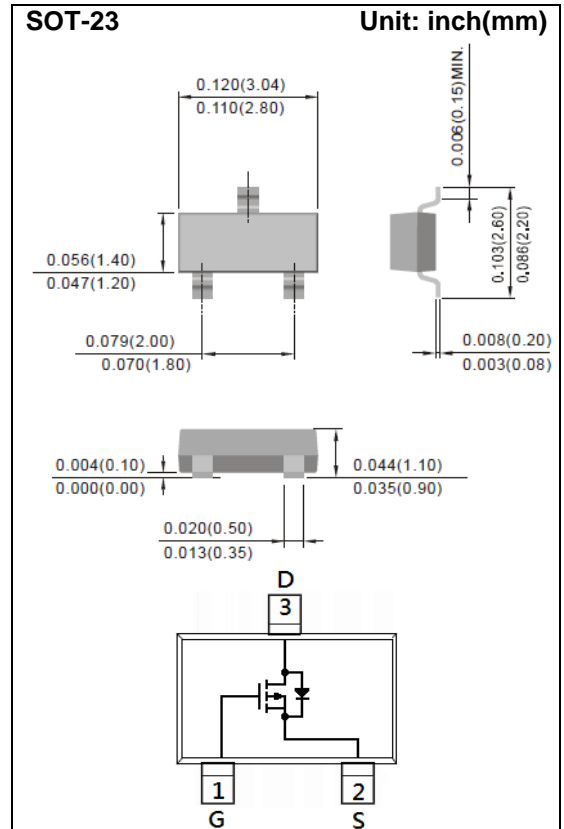
-2.9A

Features

- $R_{DS(ON)}$, $V_{GS}@-10V$, $I_D@-2.9A < 110m\Omega$
- $R_{DS(ON)}$, $V_{GS}@-4.5V$, $I_D@-1.9A < 150m\Omega$
- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 Standard

Mechanical Data

- Case : SOT-23 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0003 ounces, 0.0084 grams



Maximum Ratings and Thermal Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	+20	
Continuous Drain Current ^(Note 4)		I_D	-2.9	A
Pulsed Drain Current ^(Note 1)		I_{DM}	-11.6	
Power Dissipation	$T_a=25^\circ\text{C}$	P_D	1.25	W
	Derate above 25°C		10	mW/ $^\circ\text{C}$
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$
Typical Thermal Resistance		$R_{\theta JA}$	100	$^\circ\text{C/W}$
- Junction to Ambient ^(Note 3,4)				



PJA3409-AU

Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.31	-2.1	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-2.9A$	-	92	110	m Ω
		$V_{GS}=-4.5V, I_D=-1.9A$	-	120	150	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Dynamic (Note 5)						
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-2.9A,$ $V_{GS}=-10V$ (Note 1,2)	-	9.8	-	nC
Gate-Source Charge	Q_{gs}		-	1.5	-	
Gate-Drain Charge	Q_{gd}		-	2.2	-	
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V,$ $f=1\text{MHZ}$	-	396	-	pF
Output Capacitance	C_{oss}		-	47	-	
Reverse Transfer Capacitance	C_{rss}		-	36	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-2.9A,$ $V_{GS}=-10V,$ $R_G=6\Omega$ (Note 1,2)	-	5	-	ns
Turn-On Rise Time	t_r		-	30	-	
Turn-Off Delay Time	$t_{d(off)}$		-	25	-	
Turn-Off Fall Time	t_f		-	8	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	-1.5	A
Diode Forward Voltage	V_{SD}	$I_S=-1A, V_{GS}=0V$	-	-0.77	-1.2	V

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.
2. Essentially independent of operating temperature typical characteristics.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing.



PJA3409-AU

TYPICAL CHARACTERISTIC CURVES

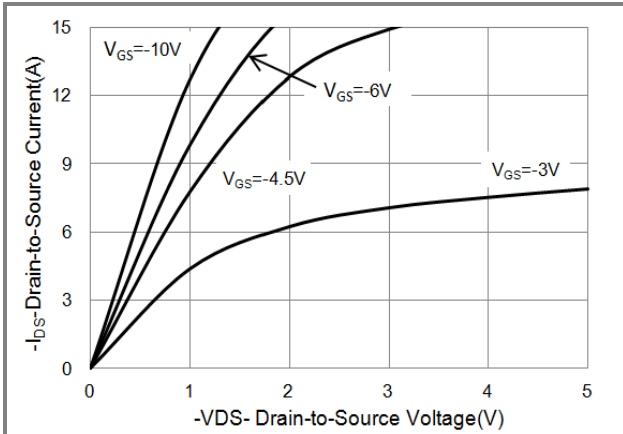


Fig.1 On-Region Characteristics

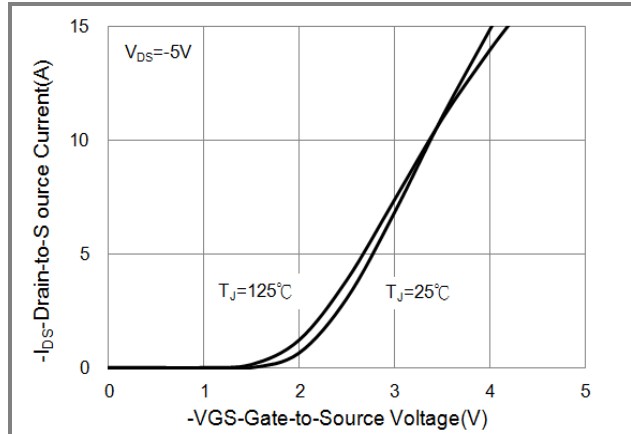


Fig.2 Transfer Characteristics

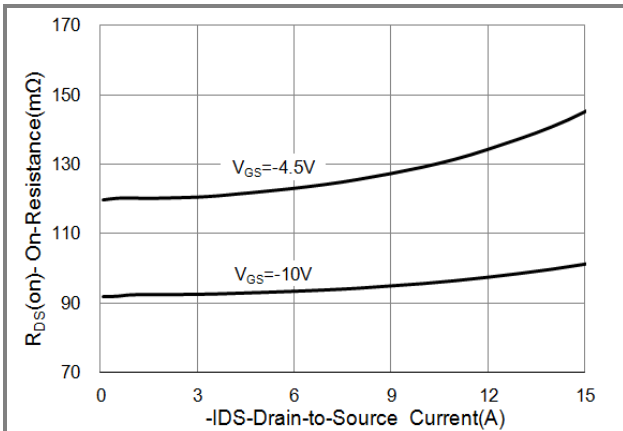


Fig.3 On-Resistance vs. Drain Current

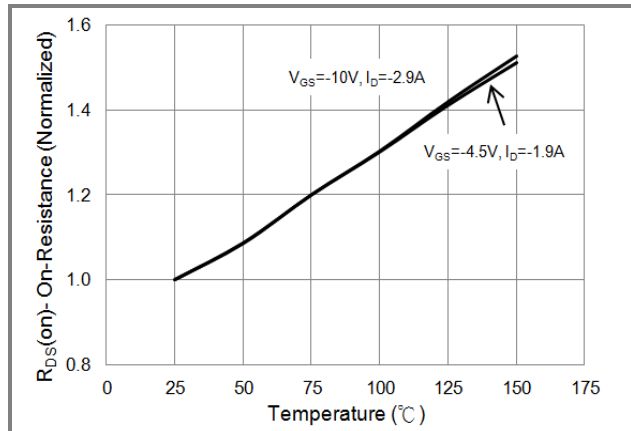


Fig.4 On-Resistance vs. Junction temperature

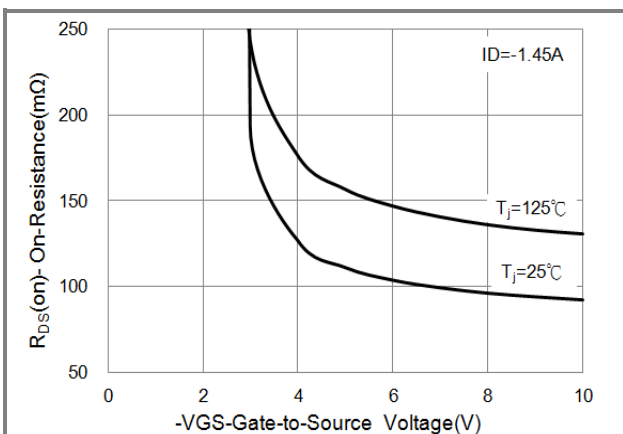


Fig.5 On-Resistance Variation with V_{GS}

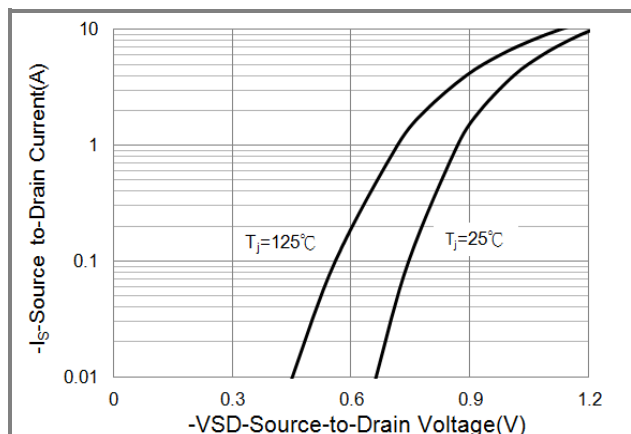


Fig.6 Body Diode Characteristics



PJA3409-AU

TYPICAL CHARACTERISTIC CURVES

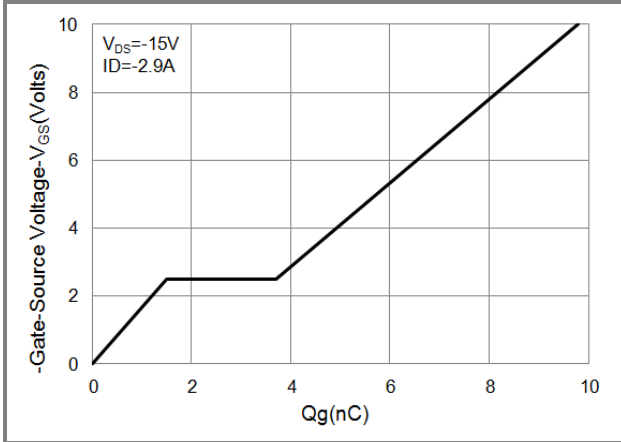


Fig.7 Gate-Charge Characteristics

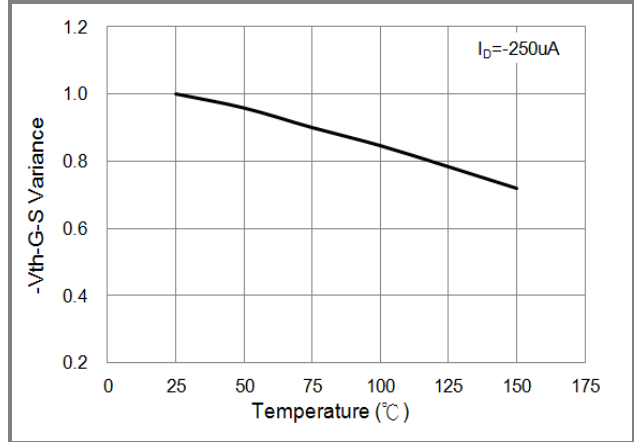


Fig.8 Threshold Voltage Variation with Temperature

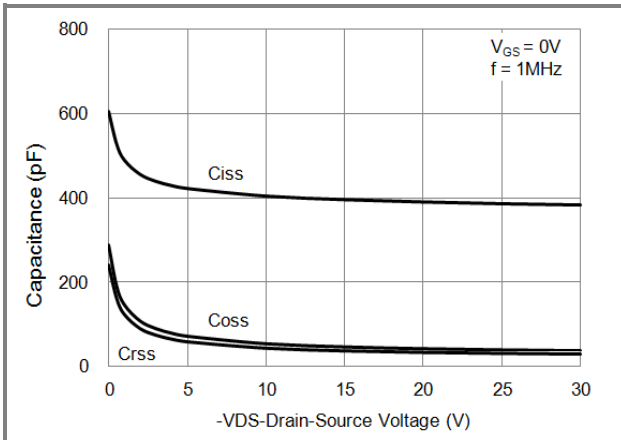


Fig.9 Capacitance vs. Drain-Source Voltage



PJA3409-AU

Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJA3409-AU_R1_000A1	SOT-23	3K pcs / 7" reel	A09	Halogen free

Packaging Information & Mounting Pad Layout

